TOSHIBA Photocoupler GaAs IRed & Photo-Transistor

TLP531,TLP532

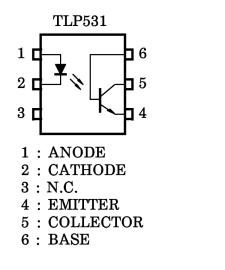
Programmable Controllers AC / DC-Input Module Solid State Relay

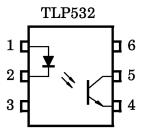
The TOSHIBA TLP531 and TLP532 consist of a photo-transistor optically coupled to a gallium arsenide infrared emitting diode in a six lead plastic DIP.

 $\mathrm{TLP532}$ is no–base internal connection for high–EMI environments.

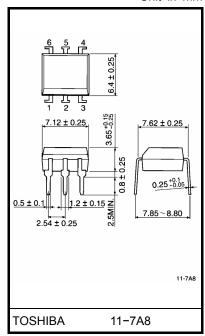
- Collector-emitter voltage: 55 V (min.)
- Current transfer ratio: 50% (min.) Rank GB: 100% (min.)
- Isolation voltage: 2500 V_{rms} (min.)
- UL recognized: UL1577, file no. E67349

Pin Configurations (top view)





1 : ANODE
 2 : CATHODE
 3 : N.C.
 4 : EMITTER
 5 : COLLECTOR
 6 : N.C.



Weight: 0.4g

Unit in mm

Absolute Maximum Ratings (Ta = 25°C)

	Characteristic	Symbol	Rating	Unit	
LED	Forward current	١ _F	70	mA	
	Forward current derating (Ta ≥ 50°C)	ΔI _F / °C	0.93	mA / °C	
	Peak forward current (100 µs pulse, 100pps)	I _{FP}	1	А	
	Reverse voltage	V _R	5	V	
	Junction temperature	Tj	125	°C	
	Collector-emitter voltage	V _{CEO}	55	V	
	Collector-base voltage (TLP531)	V _{CBO}	80	V	
Detector	Emitter-collector voltage	V _{ECO}	7	V	
	Emitter-base voltage (TLP531)	V _{EBO}	7	V	
	Collector current	Ι _C	50	mA	
	Power dissipation	PC	150	mW	
	Power dissipation derating (Ta ≥ 25°C)	ΔP _C / °C	-1.5	mW / °C	
	Junction temperature	Tj	125	°C	
Storage temperature range		T _{stg}	-55~125	°C	
Operating temperature range		T _{opr}	-55~100	°C	
Lead soldering temperature (10s)		T _{sol}	260	°C	
Total package power dissipation		PT	250	mW	
Total package power dissipation derating (Ta \ge 25°C)		ΔP _T / °C	-2.5	mW / °C	
Isolatio	n voltage (AC, 1min., R.H.≤ 60%)	BVS	2500	V _{rms}	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Recommends Operating Conditions

Characteristic	Symbol	Min.	Тур.	Max.	Unit
Supply voltage	V _{CC}	_	5	24	V
Forward current	١ _F	_	16	25	mA
Collector current	Ι _C	_	1	10	mA
Operating temperature	T _{opr}	-25	_	85	°C

Note: Recommended operating conditions are given as a design guideline to obtain expected performance of the device. Additionally, each item is an independent guideline respectively. In developing designs using this product, please confirm specified characteristics shown in this document.

Individual Electrical Characteristics (Ta = 25°C)

	Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
LED	Forward voltage	V _F	I _F = 10mA	1.0	1.15	1.3	V
	Reverse current	I _R	V _R = 5V	_	_	10	μA
	Capacitance	CT	V = 0, f = 1MHz		30	—	pF
Detector	Collector–emitter breakdown voltage	V _(BR) CEO	I _C = 0.5mA	55	_	-	V
	Emitter–collector breakdown voltage	V (BR) ECO	I _E = 0.1mA	7	_	_	V
	Collector-base breakdown voltage (TLP531)	V _(BR) CBO	I _C = 0.1mA	80	_	_	V
	Emitter-base breakdown voltage (TLP531)	V _{(BR) EBO}	I _E = 0.1mA	7	_	_	V
	Collector dark current	ICEO	V _{CE} = 24V	_	10	100	nA
			V _{CE} = 24V, Ta = 85°C	_	2	50	μA
	Capacitance (collector to emitter)	C _{CE}	V = 0, f = 1MHz	_	10	_	pF

Coupled Electrical Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Condition	Min	Тур.	Max.	Unit
		I _F = 5mA, V _{CE} = 5V	50	200	600	
		Rank	Y 50		150	
Current transfer ratio	Bank GB 400	—	300	%		
		Rank	GR 100	—	300	70
		Rank	GB 100	—	600	
		Rank	BL 200	_	600	
Collector-emitter saturation voltage	V _{CE (sat)}	I _C = 2.4mA, I _F = 8mA	_	_	0.4	V

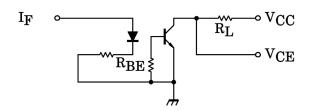
Isolation Characteristics (Ta = 25°C)

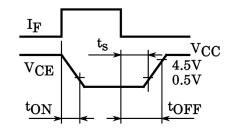
Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
Capacitance (input to output)	CS	V _S = 0, f = 1MHz	_	0.8	_	pF
Isolation resistance	R _S	V _S = 500V, R.H.≤ 60%	5×10^{10}	10 ¹⁴	_	Ω
Isolation voltage	BVS	AC, 1 minute	2500	_	-	V _{rms}

Switching Characteristics (Ta = 25°C)

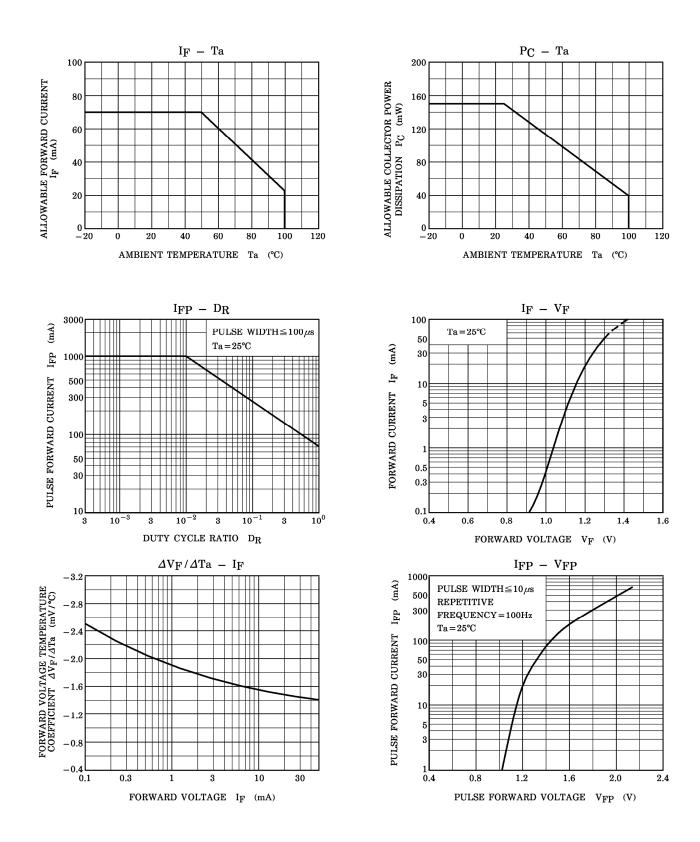
Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
Rise time	t _r	V _{CC} = 10V	_	2	—	
Fall time	t _f		_	3	_	
Turn-on time	t _{ON}	I _C = 2mA R _L = 100Ω	_	3	_	μs
Turn-off time	tOFF		_	3	_	
Turn–on time	t _{ON}	R _L = 1.9kΩ (Fig.1)	_	2	_	
Storage time	ts	R _{BE} = open	_	15	_	μs
Turn-off time	tOFF	V _{CC} = 5V, I _F = 16mA	_	25	_	
Turn–on time	t _{ON}	R _L = 1.9Ω (Fig.1)	_	2	_	
Storage time	ts	R _{BE} = 220kΩ (TLP531)	_	12	—	μs
Turn-off time	tOFF	V _{CC} = 5V, I _F = 16mA	_	20	—	

Fig. 1 Switching time test circuit

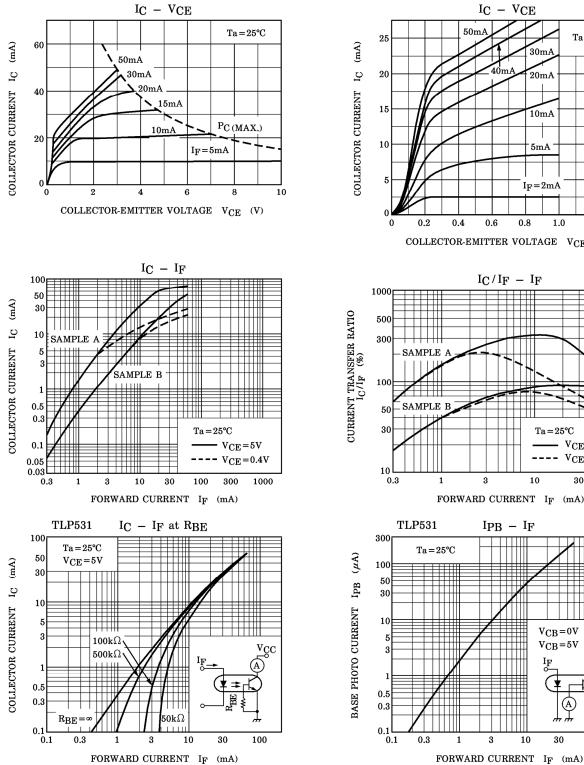




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 $Ta = 25^{\circ}C$ 30mA 20mA 10mA 5mA $I_F = 2mA$ 0.8 1.20.4 0.6 1.0 1.4 Collector-emitter voltage V_{CE} (V) IC/IF - IF+++ $Ta = 25^{\circ}C$ $V_{CE} = 5V$ $-- V_{CE} = 0.4V$ 3 10 30 100 FORWARD CURRENT IF (mA) IPB - IF $V_{CB} = 0V$ $V_{CB} = 5V$ VCB

3

10

30

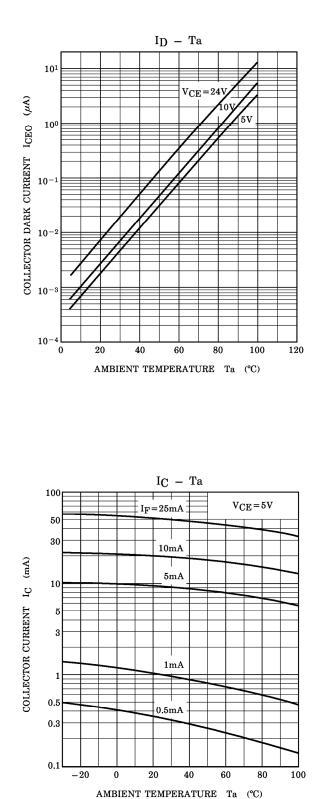
100

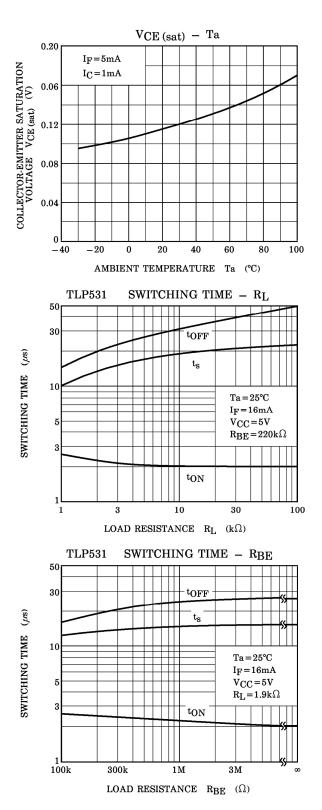
300

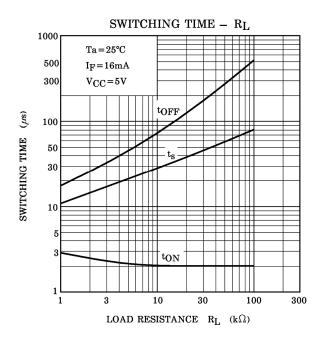
 $I_C - V_{CE}$

50mA

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